

## 2SJ620

Switching Regulator and DC-DC Converter Applications  
Motor Drive Applications

- 4-V gate drive
- Low drain-source ON resistance:  $R_{DS(ON)} = 63 \text{ m}\Omega$  (typ.)
- High forward transfer admittance:  $|Y_{fs}| = 15 \text{ S}$  (typ.)
- Low leakage current:  $I_{DSS} = -100 \text{ }\mu\text{A}$  (max) ( $V_{DS} = -100 \text{ V}$ )
- Enhancement-model:  $V_{th} = -0.8 \text{ to } -2.0 \text{ V}$  ( $V_{DS} = -10 \text{ V}$ ,  $I_D = -1 \text{ mA}$ )

### Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		$V_{DSS}$	-100	V
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		$V_{DGR}$	-100	V
Gate-source voltage		$V_{GSS}$	$\pm 20$	V
Drain current	DC (Note 1)	$I_D$	-18	A
	Pulse (Note 1)	$I_{DP}$	-72	
Drain power dissipation ( $T_c = 25^\circ\text{C}$ )		$P_D$	125	W
Single pulse avalanche energy (Note 2)		$E_{AS}$	937	mJ
Avalanche current		$I_{AR}$	-18	A
Repetitive avalanche energy (Note 3)		$E_{AR}$	12.5	mJ
Channel temperature		$T_{ch}$	150	°C
Storage temperature range		$T_{stg}$	-55 to 150	°C

### Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	1.0	°C/W

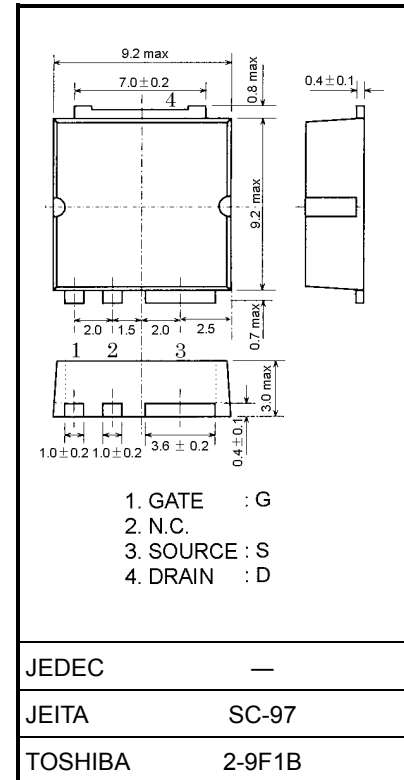
Note 1: Please use devices on condition that the channel temperature is below 150°C.

Note 2:  $V_{DD} = -50 \text{ V}$ ,  $T_{ch} = 25^\circ\text{C}$  (initial),  $L = 3.56 \text{ mH}$ ,  $R_G = 25 \text{ }\Omega$ ,  $I_{AR} = -18 \text{ A}$

Note 3: Repetitive rating: pulse width limited by maximum channel temperature

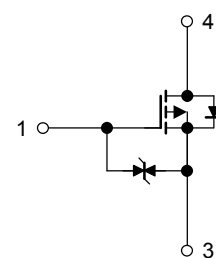
This transistor is an electrostatic sensitive device. Please handle with caution.

Unit: mm



Weight: 0.74 g (typ.)

### Circuit Configuration



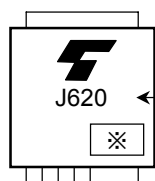
## Electrical Characteristics (Ta = 25°C)

Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		$I_{GSS}$	$V_{GS} = \pm 16\text{ V}, V_{DS} = 0\text{ V}$	—	—	$\pm 10$	$\mu\text{A}$
Drain cut-OFF current		$I_{DSS}$	$V_{DS} = -100\text{ V}, V_{GS} = 0\text{ V}$	—	—	-100	$\mu\text{A}$
Drain-source breakdown voltage		$V_{(BR)DSS}$	$I_D = -10\text{ mA}, V_{GS} = 0\text{ V}$	-100	—	—	V
Gate threshold voltage		$V_{th}$	$V_{DS} = -10\text{ V}, I_D = -1\text{ mA}$	-0.8	—	-2.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = -4\text{ V}, I_D = -9\text{ A}$	—	85	120	m $\Omega$
			$V_{GS} = -10\text{ V}, I_D = -9\text{ A}$	—	63	90	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = -10\text{ V}, I_D = -6\text{ A}$	7	15	—	S
Input capacitance		$C_{iss}$	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	—	2900	—	pF
Reverse transfer capacitance		$C_{rss}$		—	480	—	
Output capacitance		$C_{oss}$		—	1000	—	
Switching time	Rise time	$t_r$	<p><math>V_{GS}</math> 0 V, -10 V  <math>I_D = -9\text{ A}</math>  <math>V_{DS} = -10\text{ V}</math>  <math>R_L = 5.55\ \Omega</math>  <math>V_{DD} \approx -50\text{ V}</math>  <math>4.7\ \Omega</math>                      Duty <math>\leq 1\%</math>, <math>t_w = 10\ \mu\text{s}</math></p>	—	25	—	ns
	Turn-ON time	$t_{on}$		—	45	—	
	Fall time	$t_f$		—	25	—	
	Turn-OFF time	$t_{off}$		—	170	—	
Total gate charge (gate-source plus gate-drain)		$Q_g$	$V_{DD} \approx -80\text{ V}, V_{GS} = -10\text{ V}, I_D = -18\text{ A}$	—	140	—	nC
Gate-source charge		$Q_{gs}$		—	90	—	
Gate-drain ("miller") charge		$Q_{gd}$		—	50	—	

## Source-Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	$I_{DR}$	—	—	—	-18	A
Pulse drain reverse current (Note 1)	$I_{DRP}$	—	—	—	-72	A
Forward voltage (diode)	$V_{DSF}$	$I_{DR} = -18\text{ A}, V_{GS} = 0\text{ V}$	—	—	1.7	V
Reverse recovery time	$t_{rr}$	$I_{DR} = -18\text{ A}, V_{GS} = 0\text{ V},$	—	220	—	$\mu\text{s}$
Reverse recovery charge	$Q_{rr}$	$dI_{DR}/dt = 50\text{ A}/\mu\text{s}$	—	0.97	—	$\mu\text{C}$

## Marking

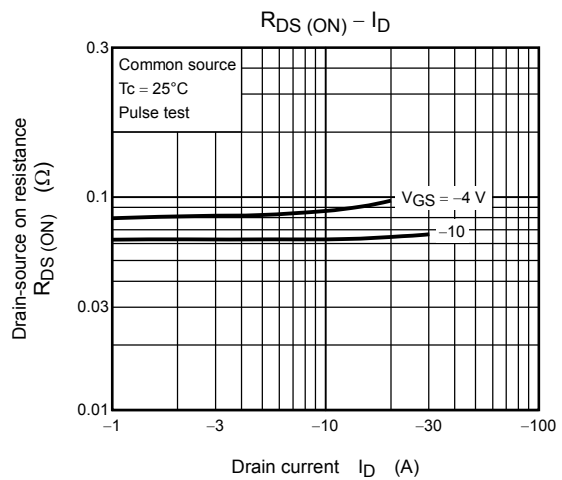
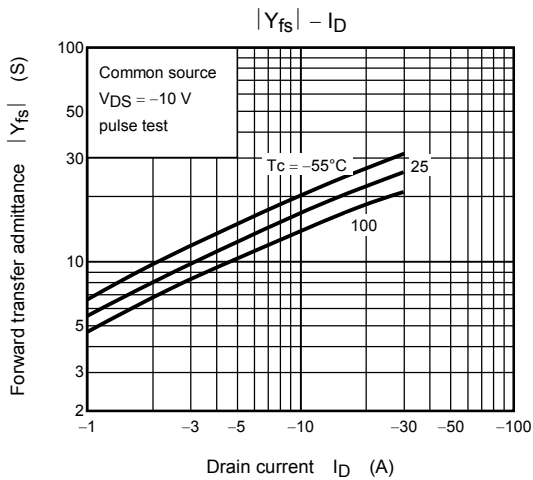
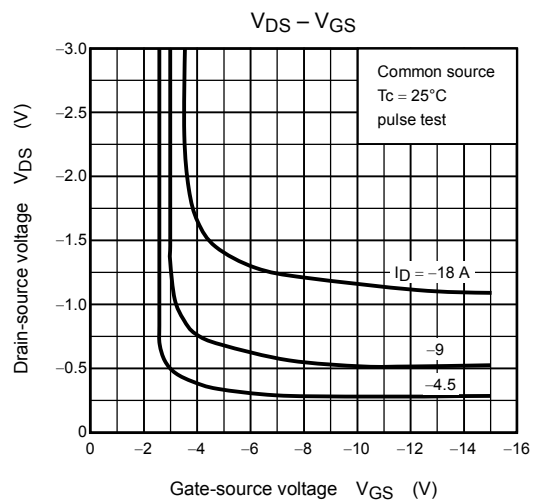
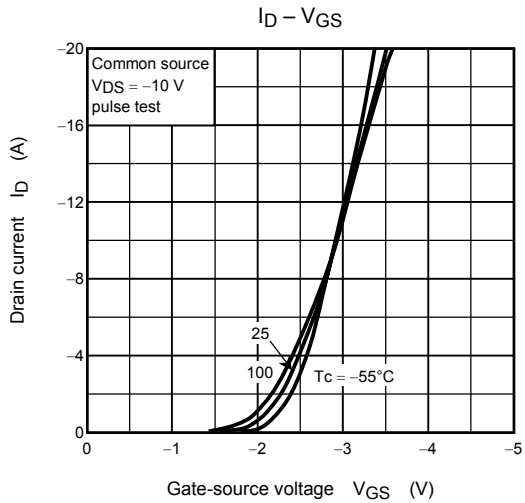
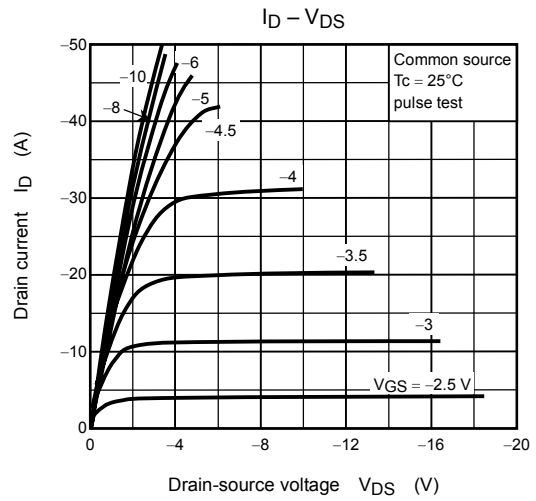
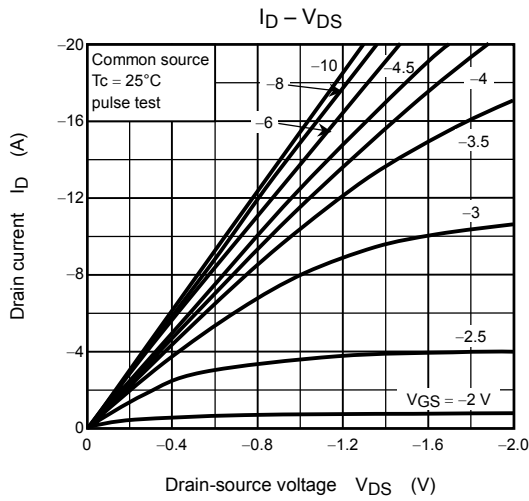


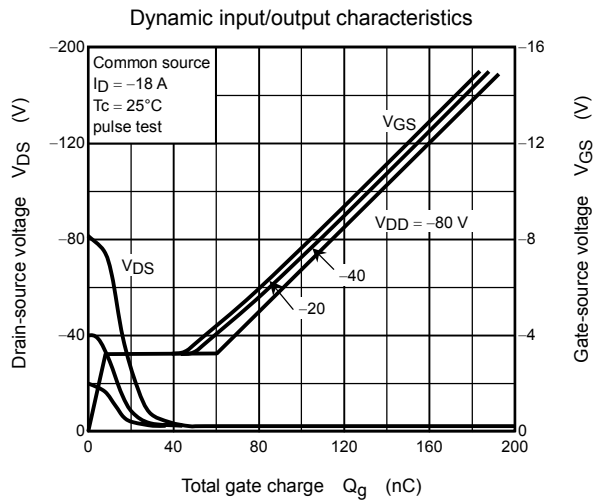
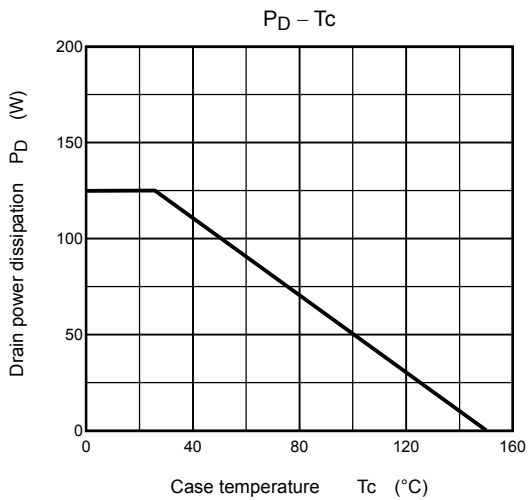
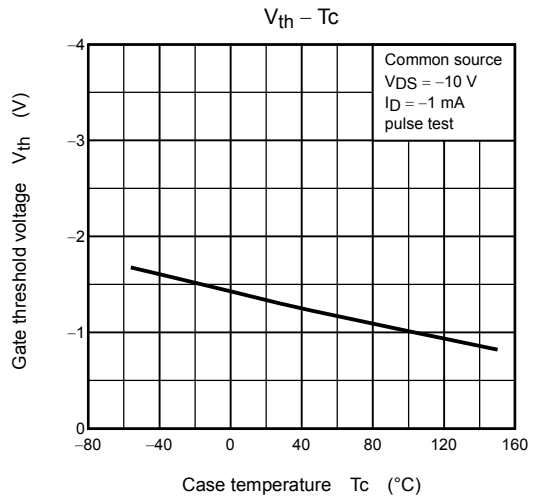
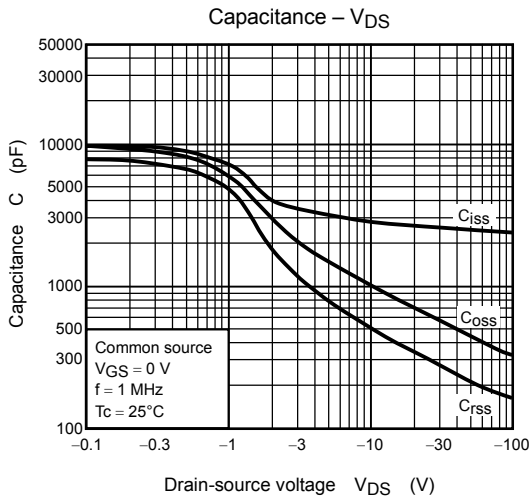
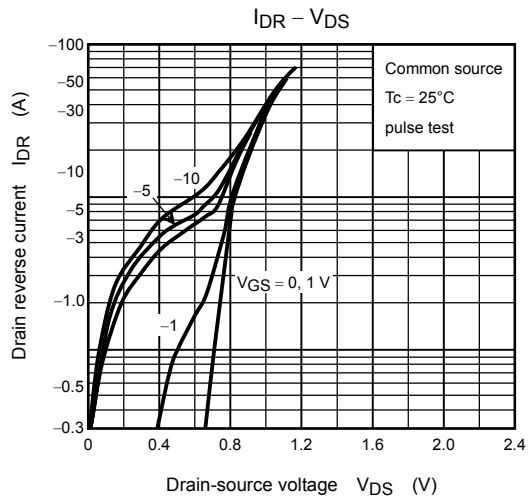
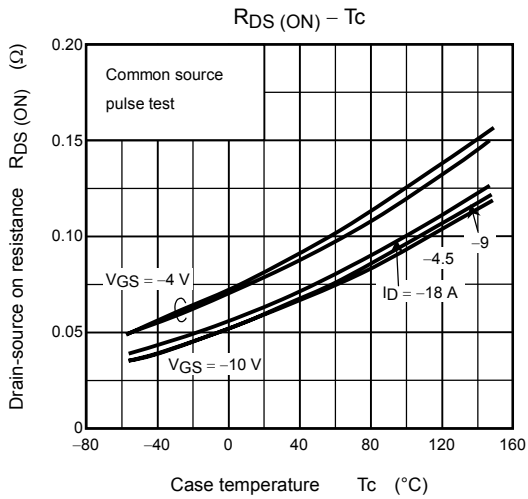
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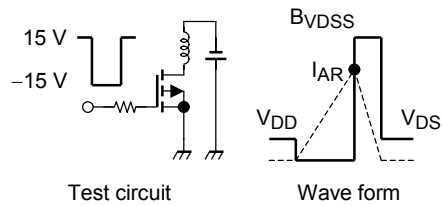
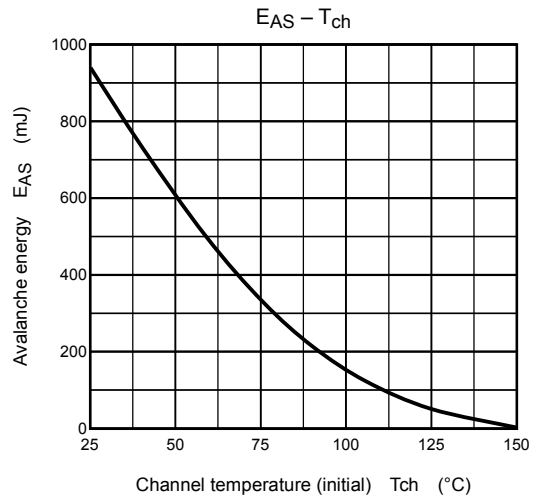
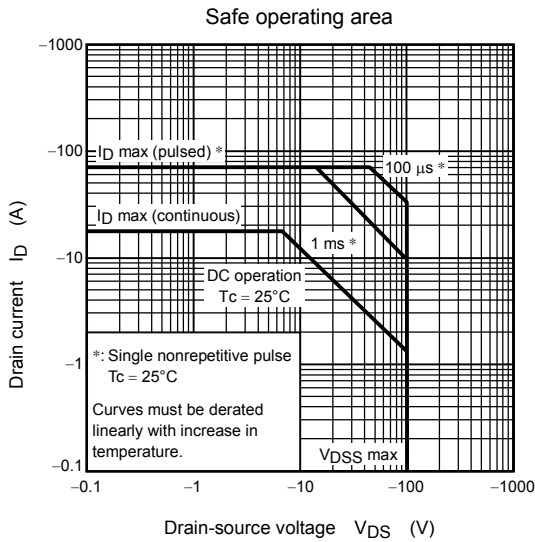
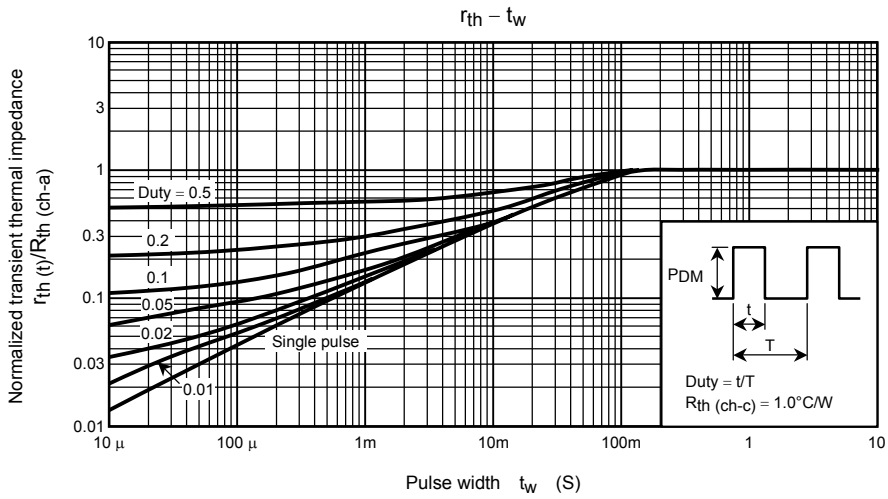
※ Lot Number

Month (starting from alphabet A)

Year (last number of the christian era)







$$R_G = 25 \Omega$$

$$V_{DD} = -50 \text{ V}, L = 3.56 \text{ mH}$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left( \frac{BVDSS}{BVDSS - V_{DD}} \right)$$

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